

L Number	Hits	Search Text	DB	Time stamp
1	22896	flip near chip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 11:43
2	10	((flip near chip) and ((chip die) with (core near (area region part portion)) with (peripher\$2 near (area region part portion))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 11:51
3	57	((flip near chip) and ((chip die) with (core near (area region part portion))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:12
4	7	("5216280" "5512765" "5581109" "5610417" "5641978" "6093942" "6144100").PN.	USPAT	2004/08/20 12:00
5	20	("3894860" "4792532" "4860087" "4978633" "5066831" "5153507" "5239448" "5258648" "5281151" "5341049" "5381307" "5391917" "5422441" "5490040" "5510758" "5523622" "5545923" "5672911" "5686764" "5703402").PN.	USPAT	2004/08/20 12:05
6	5	("4551746" "4551747" "5089881" "5218230" "5513076").PN.	USPAT	2004/08/20 12:08
7	1860	((chip die) with (core near (area region part portion)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:16
8	6	((((chip die) with (core near (area region part portion)))) and (peripher\$2 with (electrostatic near discharge (ESD))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:22
9	57	((((chip die) with (core near (area region part portion)))) and ((electrostatic near discharge) ESD))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:44
10	6	("5155065" "5300796" "5552333" "5598347" "5754826" "6374203").PN.	USPAT	2004/08/20 12:32
11	6	("5155065" "5300796" "5552333" "5598347" "5754826" "6374203").PN.	USPAT	2004/08/20 12:33
12	8874	power with ground with (arrang\$5 configur\$6 layout)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:46
13	332	((flip near chip) and (power with ground with (arrang\$5 configur\$6 layout)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:59
14	36	((flip near chip) and (power with ground with (arrang\$5 configur\$6 layout))) and ESD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:55
15	2	((flip near chip) and (power with ground with (arrang\$5 configur\$6 layout))) and ((under near ball near metallization) UBM)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:54

16	4	(power with ground with (arrang\$5 configur\$6 layout)) and ((under near ball near metallization) UBM)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:55
17	504	(flip near chip) and ((under near ball near metallization) UBM)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:55
18	5	((flip near chip) and ((under near ball near metallization) UBM)) and ESD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 13:00
19	2	((flip near chip) and ((under near ball near metallization) UBM)) and (power with ground with (arrang\$5 configur\$6 layout))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:59
20	492	((flip near chip) and ((under near ball near metallization) UBM)) and bump\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 13:00
21	425	((flip near chip) and ((under near ball near metallization) UBM)) and bump\$1) and connect\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 13:00
22	90	((flip near chip) and ((under near ball near metallization) UBM)) and bump\$1) and (connect\$3 near (structure circuit device configur\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 13:01